

/ Descriptions

WR0<50 P M M E QSQ æ M y s ll 1 Silicon NPN transistor in a TO-92LM Plastic Package.

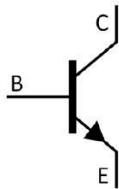
/ Features

Low $V_{CE(sat)}$, 2-3W output in complementary pair with 2SA684.

/ Applications

AF power amplifier and driver applications.

/ Equivalent Circuit



/ Pinning



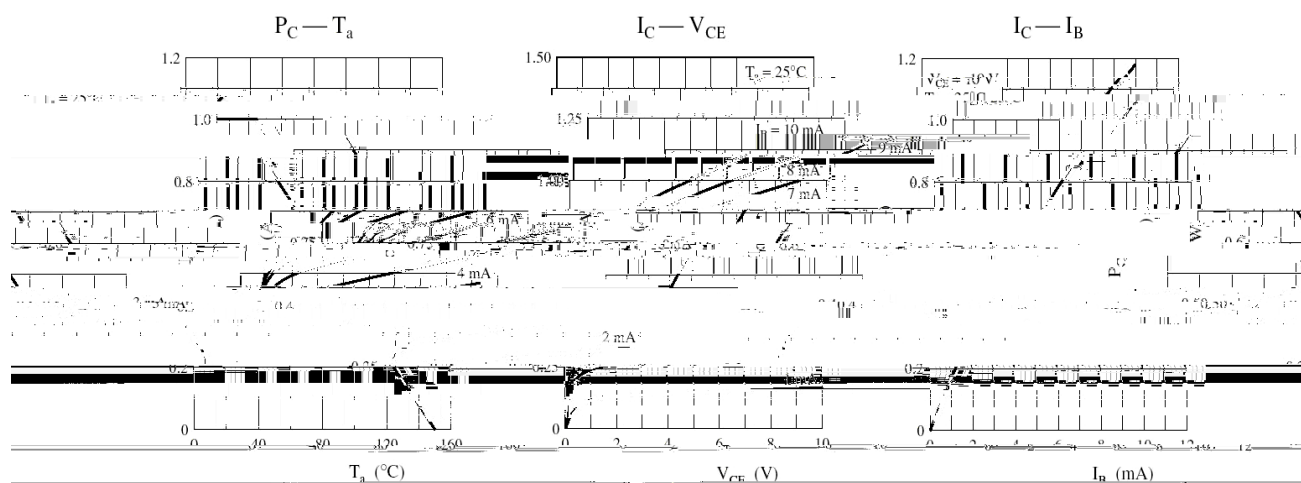
PIN1 $\times$ Base PIN 2 $\times$ Collector PIN 3 $\times$ Emitter

/ h_{FE} Classifications & Marking

h _{FE} Classifications Symbol	Q	R	S
h _{FE} Range	85~170	120~240	170~340

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	1.0	A
Collector Current – Continuous(Pulse)	I_{CP}	1.5	A
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_J	150	
Storage Temperature Range	T_{stg}	-55 150	°C

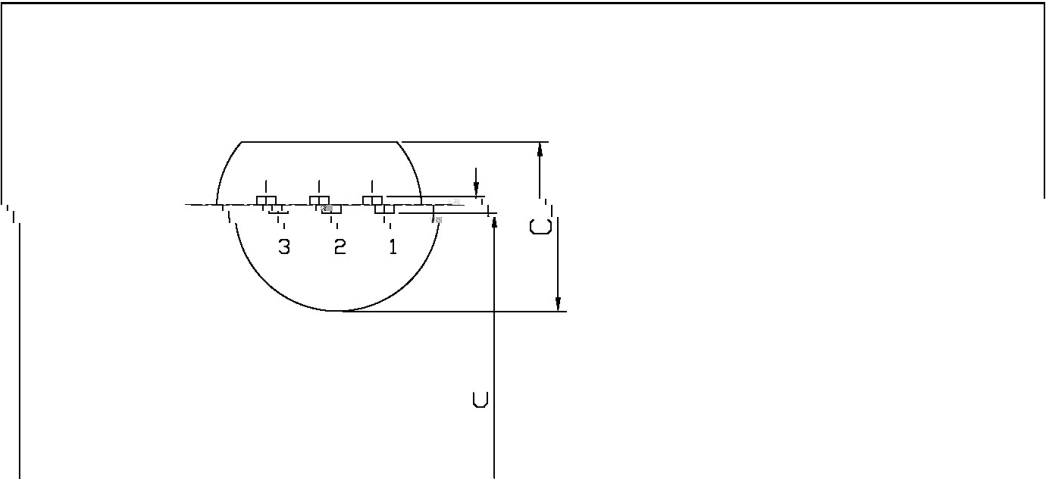
/ Electrical Characteristic Curve



/ Package Dimensions

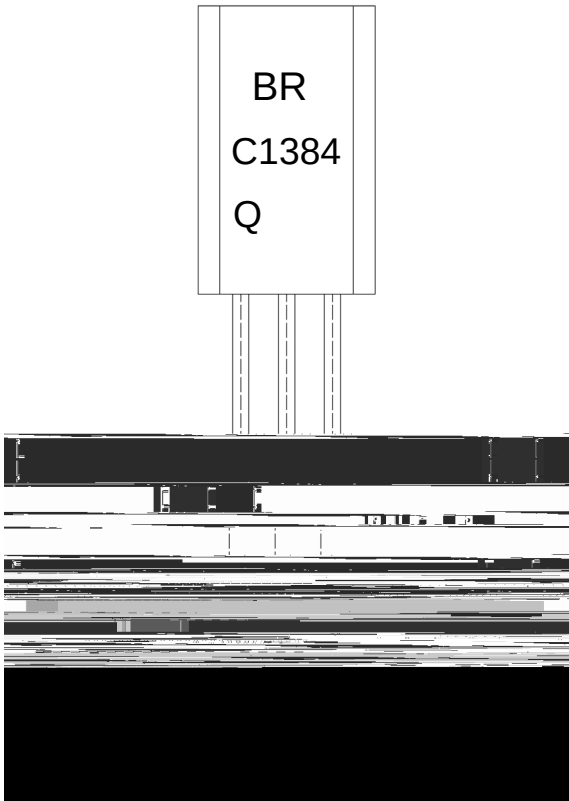
TO-92LM

Unit: mm



Symbol	Dimensions In Millimeters	
	Min	Max
A	4.7	5.1
B	1.2	1.5
C	0.8	1.0
D	0.5	0.7
E	0.5	0.7
F	0.5	0.7
G	0.5	0.7
H	0.5	0.7
I	0.5	0.7
J	0.5	0.7
K	0.5	0.7
L	0.5	0.7
M	0.5	0.7
N	0.5	0.7
O	0.5	0.7
P	0.5	0.7
Q	0.5	0.7
R	0.5	0.7
S	0.5	0.7
T	0.5	0.7
U	0.5	0.7
V	0.5	0.7
W	0.5	0.7
X	0.5	0.7
Y	0.5	0.7
Z	0.5	0.7

/ Marking Instructions



公司代码	公司代码
EU:	公司代码
F46;7	公司代码
T:	公司代码
----	公司代码
Note:	
BR:	Company Code.
C1384:	Product Type.
Q:	h _{FE} Classifications Symbol
****:	Lot No. Code,code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



б " X

1. 1. Preheating: 25~150 °C, Time: 60~90sec;
2. 2. Peak Temp.: 255 °C, Duration: 5~10sec;
3. 3. Cooling Speed: 2~10 °C/sec.

Note:

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2. Peak Temp.: 255 °C, Duration: 5~10sec.
3. Cooling Speed: 2~10 °C/sec.

/ Resistance to Soldering Heat Test Conditions

□ °C 270 °C ± 5 °C °C 10 °C ± 1 °C Temp.: 270 °C ± 5 °C Time: 10 °C ± 1 °C

/ Packaging SPEC.

“Q” T Y E / BULK

Package Type	Units				Dimension		(unit mm3)